

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor structure, comprising:  
a semiconductor chip having an edge and a surface;  
a contact pad disposed on the surface of the semiconductor chip; and  
a conductive layer disposed on ~~over a portion of the chip~~ surface of the semiconductor  
chip and in contact with the contact pad, the conductive layer having a portion that extends  
beyond ~~an~~ the edge of the semiconductor chip.
2. (Original) The structure of claim 1, wherein the conductive layer comprises a metal line.
3. (Original) The semiconductor structure of claim 1, wherein the chip comprises a device.
4. (Original) The semiconductor structure of claim 3, wherein the device comprises an integrated circuit.

5. (Original) The semiconductor structure of claim 3, wherein the device comprises a micro-electromechanical device.

6. (Cancelled)

7. (Currently Amended) The semiconductor structure of claim 1, further comprising:  
a front layer, having a first portion disposed on a ~~first~~ the surface of the semiconductor chip, and a second portion extending beyond the edge of the semiconductor chip, the conductive layer being disposed on the front layer.

8. (Original) The semiconductor structure of claim 7, wherein the front layer is a dielectric layer.

9. (Original) The semiconductor structure of claim 7, wherein the front layer is compliant.

10. (Original) The semiconductor structure of claim 7, wherein the front layer includes a bump.

11. (Currently amended) A semiconductor structure, comprising:

a semiconductor chip having a surface and an edge; and  
a contact pad disposed on the surface of the semiconductor chip; and  
a front layer, having a first portion disposed on ~~a first~~ the surface of the semiconductor chip, and a second portion extending beyond ~~an~~ the edge of the chip.

12 to 18 (Cancelled)

19. (New) The semiconductor structure of claim 7, wherein the second portion of the front layer extends beyond an edge of a second semiconductor chip.

20. (New) The semiconductor structure of claim 11, wherein the second portion of the front layer extends beyond an edge of a second semiconductor chip.

21. (New) The semiconductor structure of claim 11, further comprising:  
a conductive layer disposed on the surface of the semiconductor chip, the conductive layer having a portion that extends beyond the edge of the semiconductor chip.

22. (New) The semiconductor structure of claim 11, wherein the front layer is a dielectric layer.

23. (New) The semiconductor structure of claim 11, wherein the front layer is compliant.

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24. (New) The semiconductor structure of claim 11, wherein the front layer includes a bump.